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APPLICATION NO.	F	ILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.	
09/945,553		08/30/2001	Fernando Gonzalez	303.775US1	1842	
21186	7590	04/07/2004		EXAM	INER	
SCHWEG	MAN, LU	INDBERG, WOES	FOURSON III, GEORGE R			
P.O. BOX 2	2938					
MINNEAPOLIS, MN 55402				ART UNIT	PAPER NUMBER	

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Please find below and/or attached an Office communication concerning this application or proceeding.

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	Application No.	Applicant(s)	
	09/945,553	GONZALEZ ET AL.	
Office Action Summary	Examiner	Art Unit	
	George Fourson	2823	
The MAILING DATE of this communication appeared for Reply	ppears on the cover sheet with the	correspondence address	
A SHORTENED STATUTORY PERIOD FOR REP THE MAILING DATE OF THIS COMMUNICATION - Extensions of time may be available under the provisions of 37 CFR 1 after SIX (6) MONTHS from the mailing date of this communication. - If the period for reply specified above is less than thirty (30) days, a re - If NO period for reply is specified above, the maximum statutory perio - Failure to reply within the set or extended period for reply will, by statu Any reply received by the Office later than three months after the mail earned patent term adjustment. See 37 CFR 1.704(b).	I. 1.136(a). In no event, however, may a reply be a sply within the statutory minimum of thirty (30) di d will apply and will expire SIX (6) MONTHS fro tte, cause the application to become ABANDON	timely filed ays will be considered timely. m the mailing date of this communication IED (35 U.S.C. § 133).	1.
Status -			
1) ☐ Responsive to communication(s) filed on 12 2a) ☐ This action is FINAL. 2b) ☐ The 3) ☐ Since this application is in condition for allow closed in accordance with the practice under	nis action is non-final. vance except for formal matters, p		5
Disposition of Claims			
4) ☐ Claim(s) <u>1-66</u> is/are pending in the application 4a) Of the above claim(s) <u>2-4,7,8,13,16,23-34</u> 5) ☐ Claim(s) is/are allowed. 6) ☐ Claim(s) <u>1,5,6,9-12,14,15,17-22 and 31-33</u> is 7) ☐ Claim(s) is/are objected to. 8) ☐ Claim(s) are subject to restriction and	<u>0 and 34-66</u> is/are withdrawn from s/are rejected.	n consideration.	
Application Papers			
9) The specification is objected to by the Examination The drawing(s) filed on is/are: a) and a specificant may not request that any objection to the Replacement drawing sheet(s) including the correction. The oath or declaration is objected to by the specific specif	ccepted or b) objected to by the objected to by the objected to by the objection is required if the drawing(s) is continuous.	see 37 CFR 1.85(a). Objected to. See 37 CFR 1.121(d	d).
Priority under 35 U.S.C. § 119			
12) Acknowledgment is made of a claim for foreign a) All b) Some * c) None of: 1. Certified copies of the priority docume 2. Certified copies of the priority docume 3. Copies of the certified copies of the prapplication from the International Bure * See the attached detailed Office action for a line	nts have been received. nts have been received in Applicationity documents have been received in Received in Received in Received in Rule 17.2(a)).	ation No ved in this National Stage	
Attachment(s) 1) Notice of References Cited (PTO-892) 2) Notice of Draftsperson's Patent Drawing Review (PTO-948) 3) Information Disclosure Statement(s) (PTO-1449 or PTO/SB/0 Paper No(s)/Mail Date	4) Interview Summa Paper No(s)/Mail 5) Notice of Informa 6) Other:		

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Applicant's election of the invention of species I wherein the conditions comprise presence of a gaseous F containing compound in Paper No. 20040112 is acknowledged. Because applicant did not distinctly and specifically point out the supposed errors in the restriction requirement, the election has been treated as an election without traverse (MPEP § 818.03(a)).

Claims 1,5,6,9-12,14,15 and 17-22 are seen to either read on or be generic to the elected species.

The remaining claims require a solid F containing compound and/or require etching under conditions that reduce redeposition of volatilized metal.

Claims 31-33 link(s) inventions I and II. The restriction requirement between the linked inventions is subject to the nonallowance of the linking claim(s), claims 31-33. Upon the allowance of the linking claim(s), the restriction requirement as to the linked inventions shall be withdrawn and any claim(s) depending from or otherwise including all the limitations of the allowable linking claim(s) will be entitled to examination in the instant application. Applicant(s) are advised that if any such claim(s) depending from or including all the limitations of the allowable linking claim(s) is/are presented in a continuation or divisional application, the claims of the continuation or divisional application may be subject to provisional statutory and/or nonstatutory double patenting rejections over the claims of the instant application. Where a restriction requirement is withdrawn, the provisions of 35 U.S.C. 121 are no longer applicable. *In re Ziegler*, 44 F.2d 1211, 1215, 170 USPQ 129, 131-32 (CCPA 1971). See also MPEP § 804.01.

Claim 18 is rejected under 35 U.S.C. 112, second paragraph, as being indefinite for failing to particularly point out and distinctly claim the subject matter which applicant regards as the invention.

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There is no antecedent basis for "metal nitride barrier layer". It appears that "metal nitride" should be deleted in view of claim 19.

The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.

Claims 1,5,6,9-12,14 and 15 are rejected under 35 U.S.C. 103(a) as being unpatentable over the combination of applicant's admitted prior art (AAPA) and Mitani et al.

Applicant admits in the instant specification, pages 1-3, formation of a polycide gate stack followed by patterning and oxidation of the polysilicon portion of the stack. The process of AAPA does not include presence of gaseous NF₃.

Mitani et al discloses oxidation of polysilicon gate material in an ambient comprising NF₃ as a method of introducing F into the channel region of a MOSFET (col.41, lines 12-18).

It would have been within the scope of one of ordinary skill in the art to combine the teachings of AAPA and Mitani et al to enable the oxidation step of AAPA to be performed and further to achieve the introduction of F according to the teachings of Mitani et al.

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Claims 17 and 18-22 are rejected under 35 U.S.C. 103(a) as being unpatentable over AAPA in combination with Mitani et al as applied to claims 1,5,6,9-12,14 and 15 above, and further in view of Cunningham.

AAPA in combination with Mitani et al does not include sidewall formation or metal nitride barrier layer formation.

Cunningham discloses sidewall formation after polysilicon oxidation and metal nitride barrier layer formation in a polycide gate formation process (abstract and [0030]).

It would have been within the scope of one of ordinary skill in the art to combine the teachings of AAPA, Mitani et al and Cunningham to enable the polycide gate structure of AAPA to be formed according to the teachings of Cunningham related to obtaining greater tolerance to higher temperature annealing.

Claims 31-33 are rejected under 35 U.S.C. 103(a) as being unpatentable over AAPA in combination with Mitani et al as applied to claims 1,5,6,9-12,14 and 15 above, and further in view of Jain et al.

AAPA and Mitani et al do not disclose presence of NF3 during gate patterning.

Jain et al discloses patterning of layers to form a polycide gate electrode using NF₃ gas (col.2, lines 13-22).

It would have been within the scope of one of ordinary skill in the art to combine the teachings of AAPA, Mitani et al and Jain et al to enable the step of patterning the gate stack of AAPA to be performed and furthermore to enable removal of the ARC as disclosed by Jain (see abstract).

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Any inquiry of a general nature or relating to the status of this application should be directed to the Group Receptionist whose telephone number is (703) 308-0956 until 2/4/04. See MPEP 203.08.

Any inquiry concerning this communication or earlier communications from the examiner should be directed to examiner George Fourson whose telephone number is (571)272-1860. The examiner can normally be reached on Monday through Friday.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Olik Chaudhuri, can be reached on (571)272-1855. The fax number for this group is (571)273-0224 and the customer service number for group 2800 is 571-272-2800. Updates can be found at http://www.uspto.gov/web/info/2800.htm.

George/Fourson
Primary Examiner
Art Unit 2823

GFourson April 5, 2004